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GENERAL FEATURES

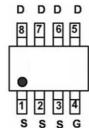
- $V_{DS} = -60V I_D = -4A$
- $R_{DS(ON)} < -98m\Omega$ @ $V_{GS}=10 \text{ V}$
- $R_{DS(ON)} < -145 \,\text{m}\Omega$ @ $V_{GS} = 4.5 V$

Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Package and Pin Configuration





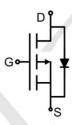
SOP-8 top view







Circuit diagram



Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage	X	V _{DSS}	-60	V
Continuous Drain Current		I _D	-4	Α
Pulsed Drain Current	(note1)	I _{DM}	-16	Α
Gate-Source Voltage		V _{GSS}	±20	V
Single Pulse Avalanche Energy	(note2)	E _{AS}	36	mJ
Avalanche Current		I _{As}	12	Α
Power Dissipation (T _C = 25°C)	(note3)	P _D	3.1	W
Operating Junction and Storage Temperature F	Range	T _J , T _{stg}	-55 To 150	°C

Thermal Data

Symbol	Parameter		Value	Unit
Rthj-a	Thermal Resistance Junction-ambient ³	Max.	40	°C/W



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Electrical Characteristics (Tj=25[°]Cunless otherwise noted)

D	0		Value				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = -250\mu A$	-60		/-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -60V, V _{GS} = 0V, T _J = 25°C	`	(- /	-1	μΑ	
		V _{DS} = -60V, V _{GS} = 0V, T _J = 150°C		-	-100		
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 20V$	- /		±100	nA	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1.0	-1.7	-3.0	V	
Drain Saures On Besistanes (Nets2)		V _{GS} = -10V, I _D = -4A		90	98	mΩ	
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = -4.5V, I_{D} = -3A$	%	100	145	mΩ	
Dynamic			5.				
Input Capacitance	C _{iss}	V _{GS} = 0V,	1	976		pF	
Output Capacitance	C _{oss}	$V_{DS} = -30V$,	-)	70			
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz	/	30			
Total Gate Charge	Q_g			24		nC	
Gate-Source Charge	Q_{gs}	$V_{DD} = -30V, I_{D} = -4A,$ $V_{GS} = -10V$		2.2			
Gate-Drain Charge	Q_{gd}		 %	3.6			
Turn-on Delay Time	t _{d(on)}			10			
Turn-on Rise Time	t _r	$V_{DD} = -30V, I_{D} = -4A,$		5		ns	
Turn-off Delay Time	t _{d(off)}	$R_G = 2.5\Omega$		35			
Turn-off Fall Time	t _f		==0	9			
Drain-Source Body Diode Characteris	stics						
Continuous Body Diode Current	Is	T = 250C			-4	A	
Pulsed Diode Forward Current	I _{SM}	T _C = 25°C			-16		
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}C$, $I_{SD} = -4A$, $V_{GS} = 0V$			-1.2	V	
Reverse Recovery Time	t _{rr}	I _F = -4A,		36		ns	
Reverse Recovery Charge	Q _{rr}	di _F /dt = 100A/µs	===	38		nC	





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Typical Electrical and Thermal Characteristics

Figure 1. Output Characteristics

(Y) tuanout 15

-10V
-6V
-4.5V
-4.5V
-3.5V
-3.5V

-3.5V
-3V
-3V
-5V
-5V
-7V
-9S, Drain-to-Source Voltage (V)

Figure 3. On-Resistance vs. Drain Current

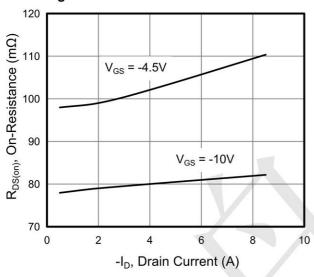


Figure 5. Threshold Voltage vs. Junction Temperature

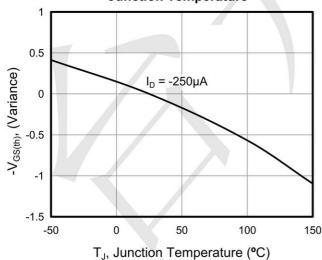


Figure 2. Transfer Characteristics

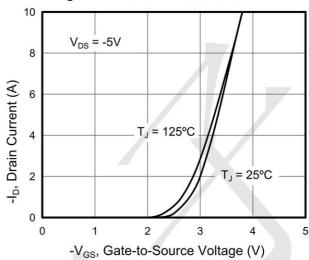


Figure 4. On-Resistance vs. Junction Temperature

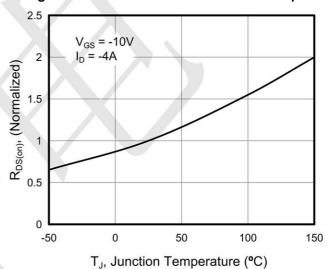
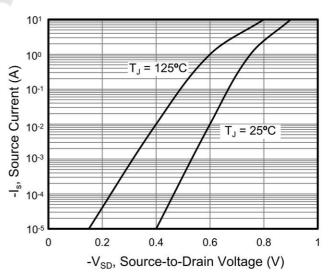


Figure 6. Body Diode Forward Voltage







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Figure 7. Capacitance

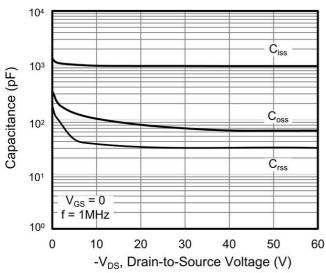


Figure 9. Transient Thermal Impedance

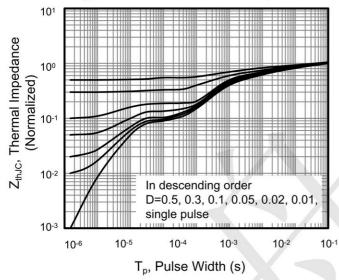


Figure 8. Gate Charge

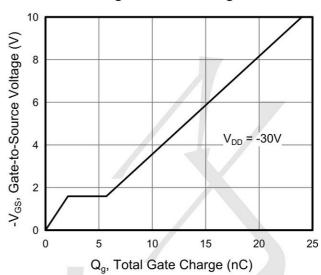
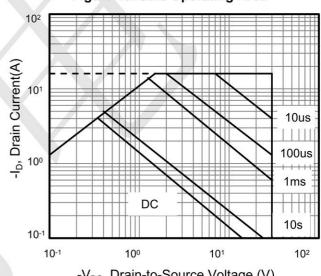


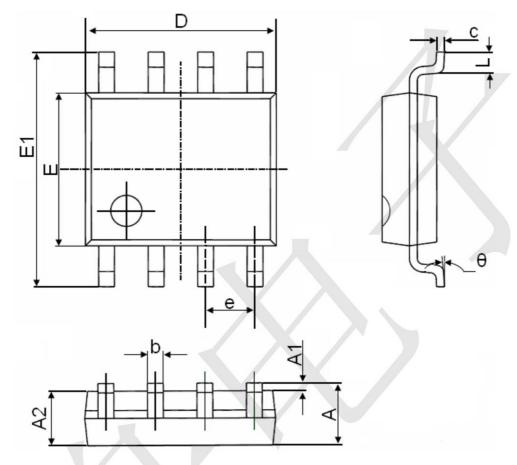
Figure 10. Safe Operating Area





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SOP-8 Package Information



Symbol	Dimensions I	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.		
Α	1.350	1.750	0.053	0.069		
A1	0.100	0.250	0.004	0.010		
A2	1.350	1.550	0.053	0.061		
b	0.330	0.510	0.013	0.020		
С	0.170	0.250	0.006	0.010		
D	4.700	5.100	0.185	0.200		
E	3.800	4.000	0.150	0.157		
E1	5.800	6.200	0.228	0.244		
е	1.270(BSC)		0.050(BSC)			
L	0.400	1.270	0.016	0.050		
θ	0°	8°	0°	8°		